

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Wendell P. Noble Attorney Docket No.: 500462.04
Filed : Concurrently herewith
Title : BASE CURRENT REVERSAL SRAM MEMORY CELL AND METHOD

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

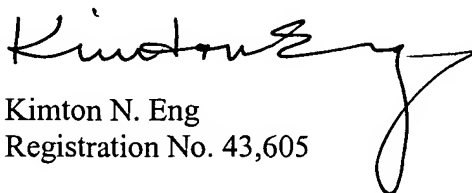
Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97 through 1.98, applicant wishes to make known to the Patent and Trademark Office the references set forth on the attached form PTO-1449. This application relies, under 35 U.S.C. § 120, on the earlier filing date of prior Application No. 10/284,984, filed October 30, 2002, which is continuation of United States Patent Application No. 09/757,683, filed January 8, 2001, issued December 3, 2002 as Patent No. 6,489,192 B2, which is a divisional of United States Patent Application No. 09/268,823, filed March 16, 1999, issued November 6, 2001 as Patent No. 6,313,490 B1. The references listed on the attached Form PTO-1449 were submitted to and/or cited by the Patent and Trademark Office in these prior applications and, therefore, are not required to be provided in this application. If the Examiner wishes, copies will be provided upon request. Although the aforesaid references are made known to the Patent and Trademark Office in compliance with applicant's duty to disclose all information he is aware of which is believed relevant to the examination of the above-identified application, applicant believes that his invention is patentable.

Please acknowledge receipt of this Information Disclosure Statement and kindly make the cited references of record in the above-identified application.

Respectfully submitted,

DORSEY & WHITNEY LLP

A handwritten signature in black ink, appearing to read "Kimton N. Eng", with a long, sweeping horizontal stroke extending to the right.

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Enclosure:

Form PTO-1449

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FORM PTO-1449
(REV. 7-80)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.
500462.04

APPLICATION NO.
Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT(S)
Wendell P. Noble

FILING DATE
Concurrently herewith

GROUP ART UNIT
Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	4,810,667	03/07/89	Zorinsky et al.	437	62	
	AB	4,881,105	11/14/89	Davari et al.	357	23.4	
	AC	5,194,396	03/16/93	Kim et al.	437	31	
	AD	5,574,299	11/12/96	Kim	257	296	
	AE	5,592,005	01/07/97	Floyd et al.	257	331	
	AF	5,594,683	01/14/97	Chen et al.	365	177	
	AG	6,075,272	06/13/00	Forbes et al.	257	378	
	AH	6,229,161 B1	05/08/01	Nemati et al.	257	133	
	AI	6,489,192 B2	12/03/02	Noble	438	202	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AJ	JP359232437A	12/27/84	Japan			X	
	AK	10135235	05/22/98	Japan			X	

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AL	S.D. Malaviya, "Single Device DC Stable Memory Cell", IBM Technical Disclosure Bulletin, Vol. 20, No. 9, February 1978, IBM Corp. 1978, 3492-3494.
	AM	Jack Y.C. Sun, "CMOS Technology for 1.8V and Beyond", Semiconductor Research and Development Center, IBM Corporation, pp. 293-297.
	AN	Sakui, Koji et al., "A New Static Memory Cell Based on Reverse Base Current (RBC) Effect of Bipolar Transistor", ULSI Research Center, Toshiba Corporation, Japan, 44-IEDM 88 (4 pages).
	AO	Van der Wagt, J.P., et al., "RTD/HFET Low Standby Power SRAM Gain Cell", IEEE Electron Device Letters, Vol. 19, No. 1, January 1998, pp. 6-9.
	AP	Verdonckt-Vandebroek, Sophie et al., "High-Gain Lateral Bipolar Action in a MOSFET Structure", IEEE Transactions on Electron Devices, Vol. 38, No. 11, November 1991, pp. 2487-2496.

EXAMINER

DATE CONSIDERED

* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).